

C1
(d) forming a second insulating film on the second wiring layer,

(e) [the step of] forming a first etching mask having openings on the second insulating film, and

(f) forming a first contact hole on the second wiring layer in the second insulating film and a second contact hole on the first wiring layer in the first and the second insulating films by an etching method through the openings of the first etching mask, wherein the etching ratio of the first film by the etching method is smaller than the etching ratio of the first and second insulating films by the etching method.

Claim 2, line 3, delete "the step of".

Please add the following new claim:

C2
-- 17. A process for manufacturing a semiconductor integrated circuit device according to claim 1, wherein the etching method forms the first and second contact holes simultaneously. --

REMARKS

Entry of this amendment prior to examination is respectfully requested.

By the present amendment, claims 1 and 2 have been amended to provide minor language clarification. Claim 17 has